

**/ Descriptions**

SOT-23          NPN                          Silicon NPN transistor in a SOT-23 Plastic Package.

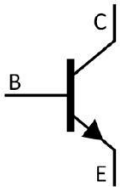
**/ Features**

S8550MG  
Complementary pair with S8550MG,HF Product.

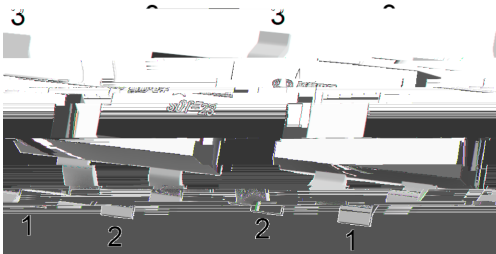
**/ Applications**

Power amplifier applications.

**/ Equivalent Circuit**



**/ Pinning**



PIN1 Base      PIN 2 Emitter      PIN 3 Collector

**/ hFE Classifications & Marking**

hFE Classifications Symbol	B	C	D
h <sub>FE(1)</sub> Range	85 160	120 200	160 300
Marking	GY3B	GY3C	GY3D

**/ Absolute Maximum Ratings(Ta=25 )**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V <sub>CB0</sub>	40	V
Collector to Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter to Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	800	mA
Base Current	I <sub>B</sub>	200	mA
Collector Power Dissipation	P <sub>C</sub>	200	mW
Junction Temperature	T <sub>j</sub>	150	
Storage Temperature Range	T <sub>stg</sub>	-55 150	

**/ Electrical Characteristics(Ta=25 )**

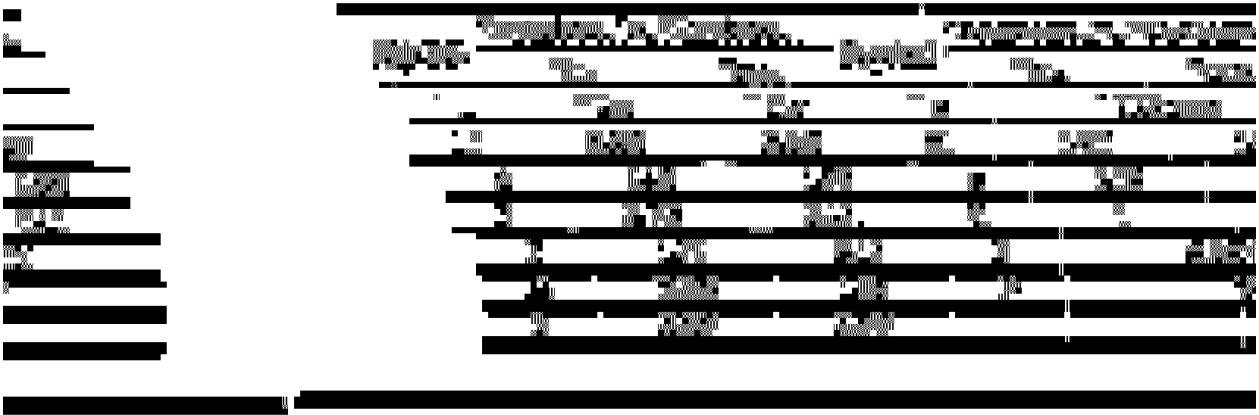
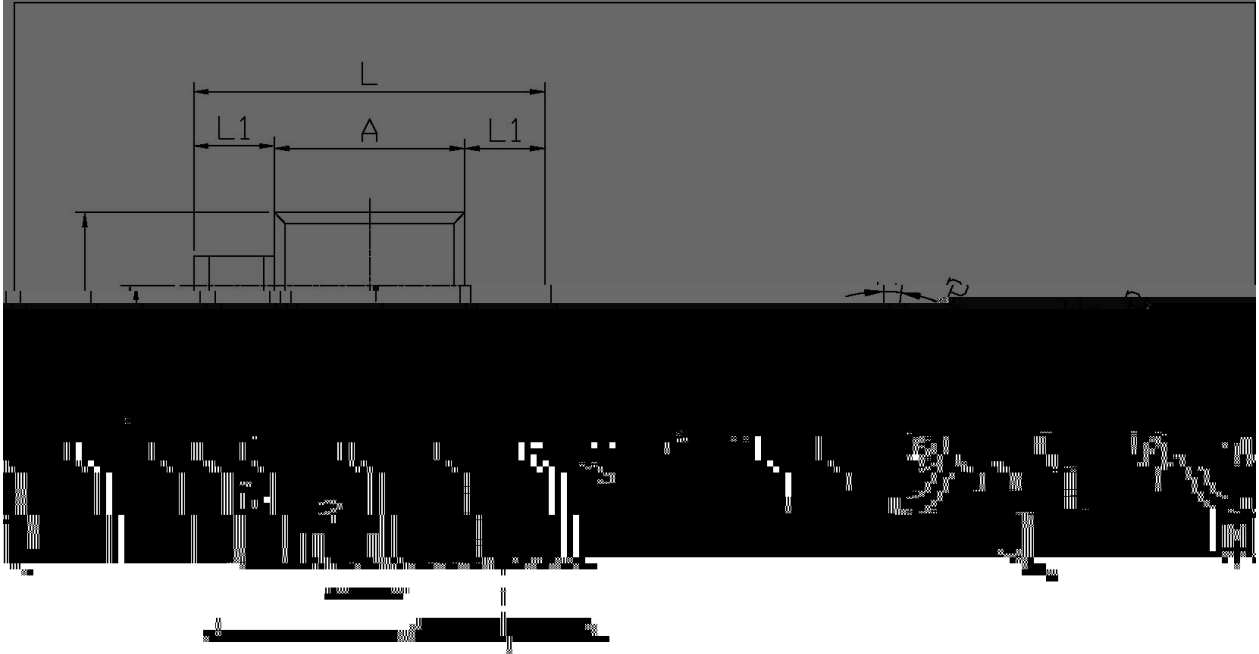
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V <sub>CB0</sub>	I <sub>C</sub> =0.1mA I <sub>E</sub> =0	40			V
Collector to Emitter Breakdown Voltage	V <sub>CEO</sub>	I <sub>C</sub> =2.0mA I <sub>B</sub> =0	25			V
Emitter to Base Breakdown Voltage	V <sub>EBO</sub>	I <sub>E</sub> =0.1mA I <sub>C</sub> =0	6.0			V
Collector Cut-Off Current	I <sub>CB0</sub>	V <sub>CB</sub> =35V I <sub>E</sub> =0			0.1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =6.0V I <sub>C</sub> =0			0.1	μA
DC Current Gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1.0V I <sub>C</sub> =100mA	85		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1.0V I <sub>C</sub> =500mA	40			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =1.0V I <sub>C</sub> =5.0mA	45			
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =500mA I <sub>B</sub> =50mA		0.28	0.5	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =500mA I <sub>B</sub> =50mA		0.98	1.2	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =1.0V I <sub>C</sub> =10mA		0.66	1.0	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =10V I <sub>C</sub> =50mA	100	190		MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V I <sub>E</sub> =0 f=1.0MHz		9.0		pF

**S8050MG**  
Rev.1 May.-2023

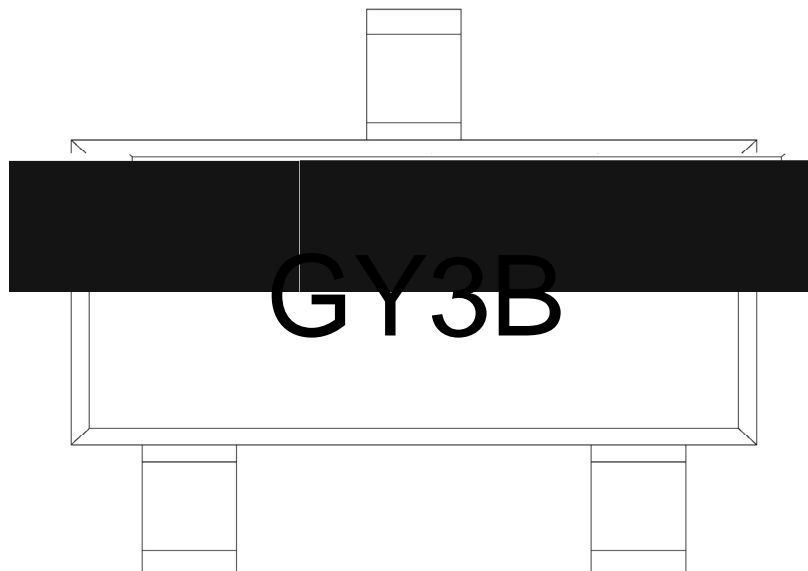
/ Package Dimensions

SOT-23

单位: mm



**/ Marking Instructions**



G

Y3

B            h<sub>FE</sub>

Note:

G            HF Product Code

Y3          Product Type Code

B            h<sub>FE</sub> Classifications Symbol Code

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Note:

- |   |         |           |   |
|---|---------|-----------|---|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180 , Time:60~90sec.   |
| 2 | 245±5   | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 |         |           |   |